

Vishay Semiconductors

AAP Gen 7 (TO-240AA) Power Modules Thyristor/Thyristor, 105 A



PRIMARY CHARACTERISTICS						
I _{T(AV)}	105 A					
Туре	Modules - thyristor, standard					
Package	AAP Gen 7 (TO-240AA)					

MECHANICAL DESCRIPTION

The AAP Gen 7 (TO-240AA), new generation of AAP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- High voltage
- Industrial standard package
- UL approved file E78996
- Low thermal resistance
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- · Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{T(AV)}	85 °C	105				
I _{T(RMS)}		165	Α			
I _{TSM}	50 Hz	2000	A			
	60 Hz	2094				
l ² t	50 Hz	20	kA ² s			
1-1	60 Hz	18.26	KA-S			
I ² √t		200	kA²√s			
V _{RRM}	Range	400 to 1600	V			
T _{Stg}		-40 to +130	°C			
T _J		-40 to +130	°C			

VS-VSKU105.., VS-VSKV105.. Series

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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 130 °C mA				
	04	400	500	400					
VS-VSK.105	08	800	900	800	15				
V3-V3K.103	12	1200	1300	1200	15				
	16	1600	1700	1600	1				

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	180° conduction T _C = 85 °C	180° conduction, half sine wave, T _C = 85 °C		105	Α
Maximum continuous RMS on-state current	I	DC			165	
Maximum continuous nivio on-state current	I _{T(RMS)}	T _C			78	°C
		t = 10 ms	No voltage	Sinusoidal	2000	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	half wave,	2094	۸
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	initial T _J =	1682	Α
		t = 8.3 ms	reapplied	T _J maximum	1760	
	l ² t	t = 10 ms	No voltage		20	kA ² s
Marrian 124 for fraince		t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	18.26	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I ² √t for fusing	I ² √t ⁽¹⁾		t = 0.1 ms to 10 ms, no voltage reapplied T ₁ = T ₁ maximum			kA²√s
Marian and a of the calculation	(0)	Low level (3)	T _J = T _J maximum		0.98	V
Maximum value of threshold voltage	V _{T(TO)} (2)	High level (4)			1.12	
Maximum value of on-state	w (2)	Low level (3)	T T mayin		2.7	~ 0
slope resistance	r _t ⁽²⁾	High level (4)	$T_J = T_J$ maximum		2.34	mΩ
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$	I _{T(AV)} T _J = 25 °C		1.8	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25$ °C, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500$ mA, $t_r < 0.5$ μ s, $t_p > 6$ μ s		150	A/µs	
Maximum holding current	I _H	T _J = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	Ι _L	T _J = 25 °C, and	ode supply = 6 \	/, resistive load	400	

Notes

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

^{(3) 16.7 %} $\times \pi \times I_{AV} < I < \pi \times I_{AV}$

⁽⁴⁾ $I > \pi \times I_{AV}$

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TRIGGERING					
PARAMETER	SYMBOL	TEST CO	ONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			12	W
Maximum average gate power	P _{G(AV)}			3.0	VV
Maximum peak gate current	I _{GM}			3.0	Α
Maximum peak negative gate voltage	- V _{GM}			10	
		T _J = - 40 °C	Anode supply = 6 V resistive load	4.0	V
Maximum gate voltage required to trigger	V_{GT}	T _J = 25 °C		2.5	
		T _J = 125 °C		1.7	
		T _J = - 40 °C		270	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V	150	mA
		T _J = 125 °C	Tesistive load	80	
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V
Maximum gate current that will not trigger	I _{GD}	T _J = 125 °C, rated V _{DRM} applied		6	mA

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 130 °C, gate open circuit	20	mA				
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 130 °C, linear to 0.67 V_{DRM}	1000	V/µs				

THERMAL AND MECH	THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to 130	°C	
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.22	°C/W	
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	C/VV	
Mounting torque ± 10 %	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm	
busbar			3 hours to allow for the spread of the compound.	3	INIII	
Approximate weight				75	g	
Approximate weight	Approximate weight			2.7	oz.	
Case style			JEDEC®	AAP Gen 7	(TO-240AA)	

△R CONDUCTION PER JUNCTION											
DEVICES	8	SINE HALF WAVE CONDUCTION					CTANGUL	AR WAVE C	CONDUCTION	NC	UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.105	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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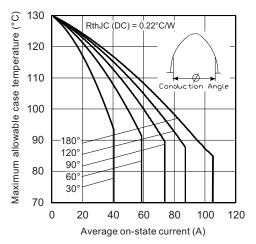


Fig. 1 - Current Ratings Characteristics

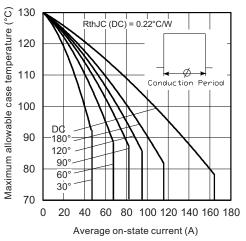


Fig. 2 - Current Ratings Characteristics

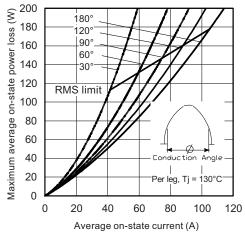


Fig. 3 - On-State Power Loss Characteristics

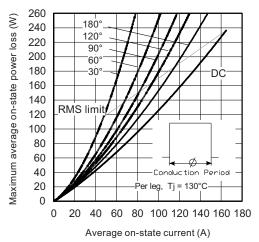


Fig. 4 - On-State Power Loss Characteristics

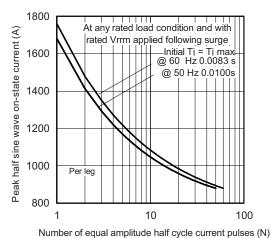


Fig. 5 - Maximum Non-Repetitive Surge Current

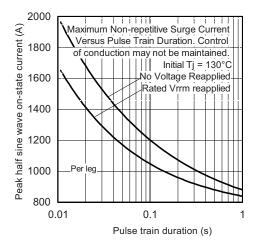


Fig. 6 - Maximum Non-Repetitive Surge Current

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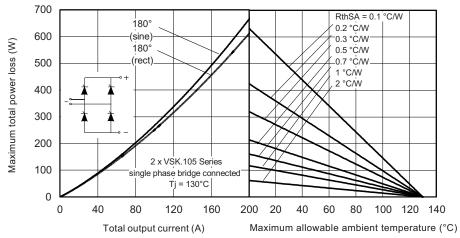


Fig. 7 - On-State Power Loss Characteristics

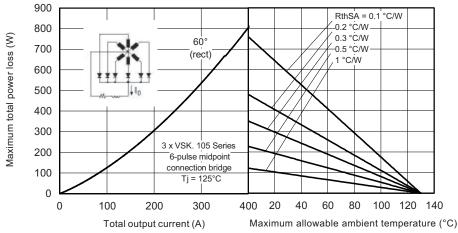


Fig. 8 - On-State Power Loss Characteristics

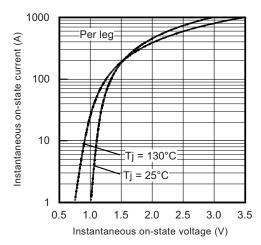


Fig. 9 - On-State Voltage Characteristics

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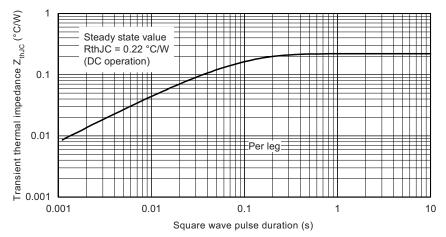


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics

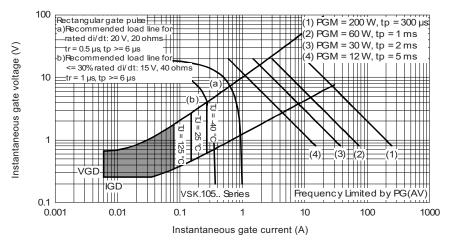
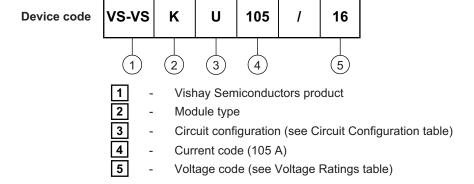


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172

VS-VSKU105.., VS-VSKV105.. Series

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CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs common cathodes	U	VSKU (1) 1 2 (2) (3) (3) (3) (4) (5) (7) (6)
Two SCRs common anodes	V	VSKV (1) (2) (3) (3) (3) (3) (4) (5) (7) (6)

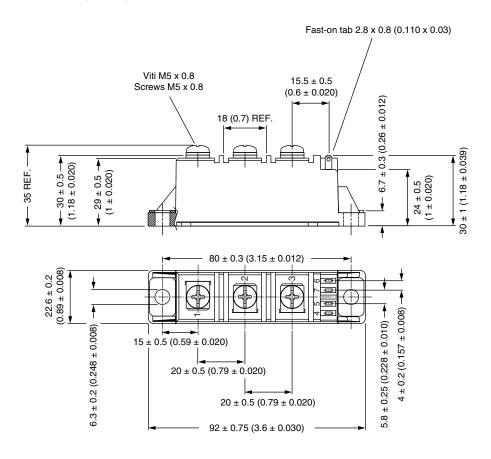
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





Legal Disclaimer Notice

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